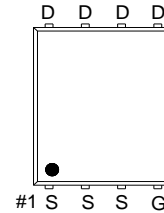
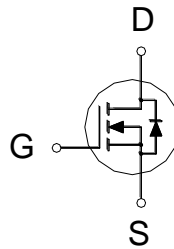




PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
100V	8.2mΩ	69A



G. GATE
D. DRAIN
S. SOURCE

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ °C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	$T_C = 25\text{ °C}$	I_D	69	A
	$T_C = 100\text{ °C}$		48	
Pulsed Drain Current ¹		I_{DM}	150	
Continuous Drain Current	$T_A = 25\text{ °C}$	I_D	15	
	$T_A = 70\text{ °C}$		13	
Avalanche Current		I_{AS}	19	
Avalanche Energy	$L = 1\text{mH}$	E_{AS}	180	mJ
Power Dissipation	$T_C = 25\text{ °C}$	P_D	93	W
	$T_C = 100\text{ °C}$		46	
Power Dissipation ³	$T_A = 25\text{ °C}$	P_D	5	W
	$T_A = 70\text{ °C}$		3.5	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 175	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ²	$t \leq 10\text{s}$	$R_{\theta JA}$		30	°C / W
Junction-to-Ambient ²	Steady-State	$R_{\theta JA}$		56	
Junction-to-Case	Steady-State	$R_{\theta JC}$		1.6	

¹Pulse width limited by maximum junction temperature.

²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25\text{ °C}$.

³The Power dissipation is based on $R_{\theta JA} t \leq 10\text{s}$ value.

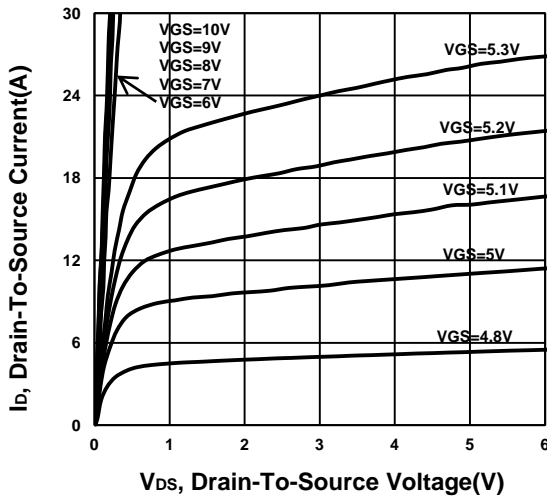
ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	100			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2	3	4	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 100V, V _{GS} = 0V			1	μA
		V _{DS} = 100V, V _{GS} = 0V, T _J = 55 °C			10	
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = 10V, I _D = 14A		6.4	8.2	mΩ
Forward Transconductance ¹	g _{fs}	V _{DS} = 5V, I _D = 14A		45		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 50V, f = 1MHz		3490		pF
Output Capacitance	C _{oss}			283		
Reverse Transfer Capacitance	C _{rss}			17.5		
Gate Resistance	R _g	V _{GS} = 0V, V _{DS} = 0V, f = 1MHz		1.7		Ω
Total Gate Charge ²	Q _g	V _{DS} = 50V, V _{GS} = 10V, I _D = 14A		55		nC
Gate-Source Charge ²	Q _{gs}			17		
Gate-Drain Charge ²	Q _{gd}			15		
Turn-On Delay Time ²	t _{d(on)}	V _{DS} = 50V, I _D ≅ 14A, V _{GS} = 10V, R _{GEN} = 6Ω		26		nS
Rise Time ²	t _r			67		
Turn-Off Delay Time ²	t _{d(off)}			52		
Fall Time ²	t _f			55		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current	I _S				69	A
Forward Voltage ¹	V _{SD}	I _F = 14A, V _{GS} = 0V			1.2	V
Reverse Recovery Time	t _{rr}	I _F = 14A, di _F /dt = 100A / μS		43		nS
Reverse Recovery Charge	Q _{rr}				73	

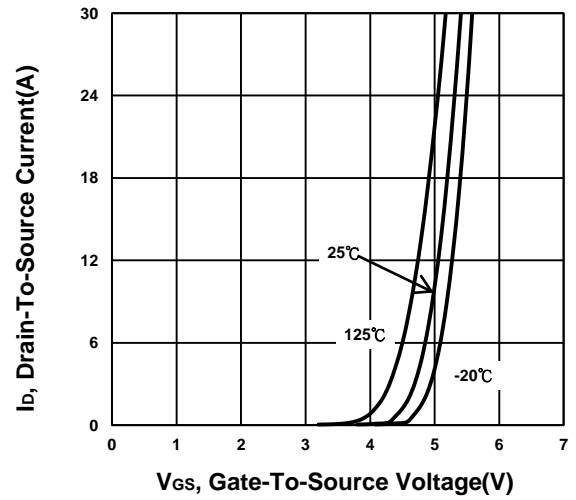
¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

²Independent of operating temperature.

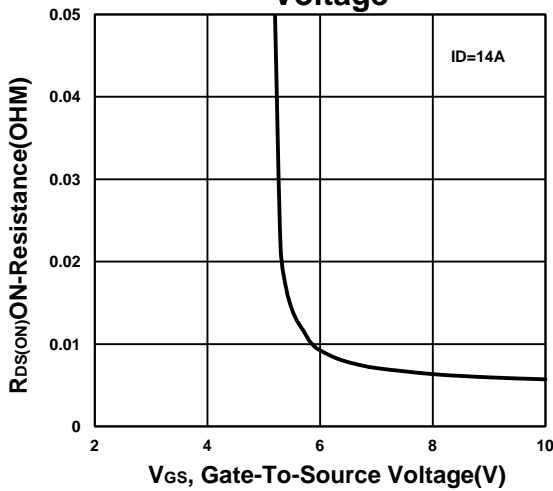
Output Characteristics



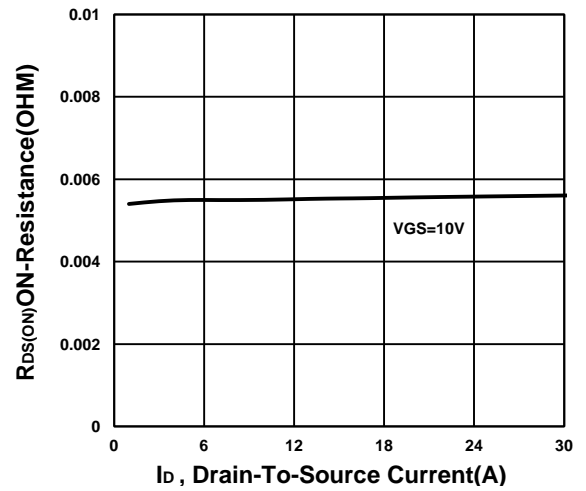
Transfer Characteristics



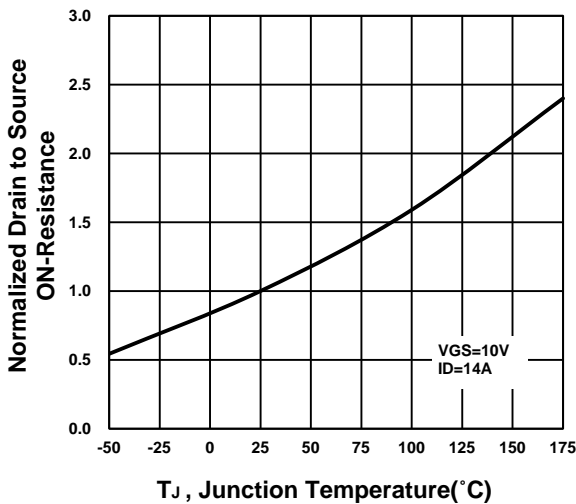
On-Resistance VS Gate-To-Source Voltage



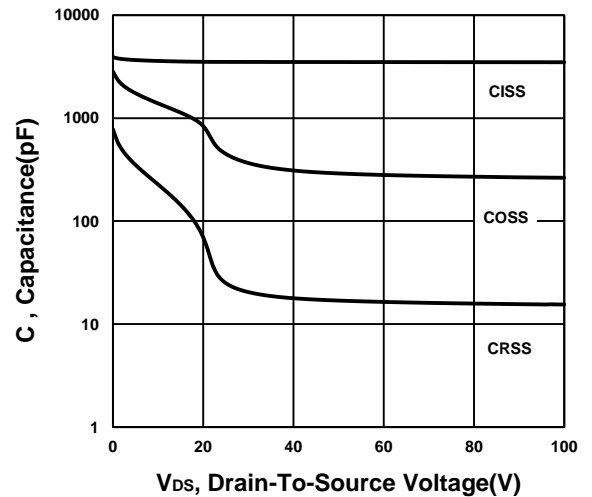
On-Resistance VS Drain Current



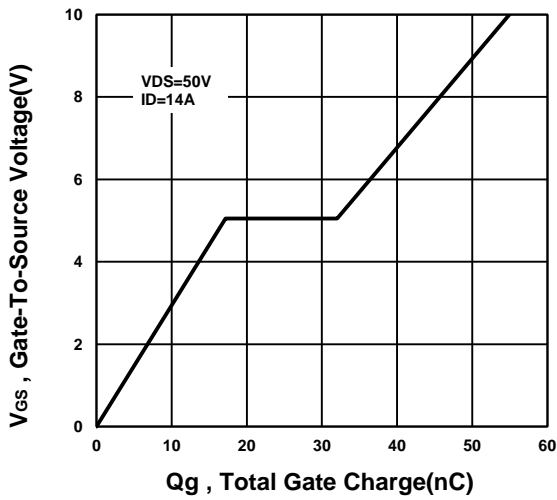
On-Resistance VS Temperature



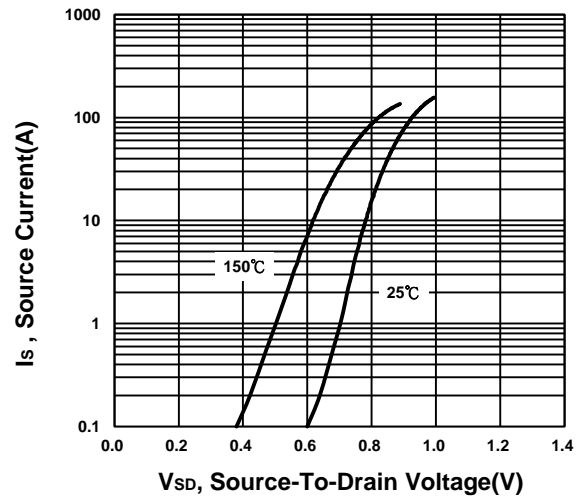
Capacitance Characteristic



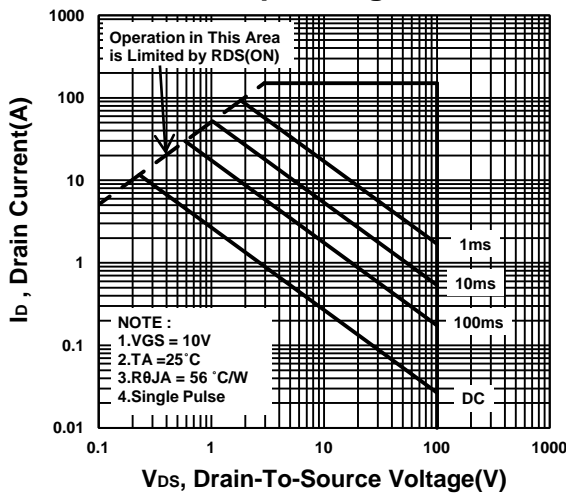
Gate charge Characteristics



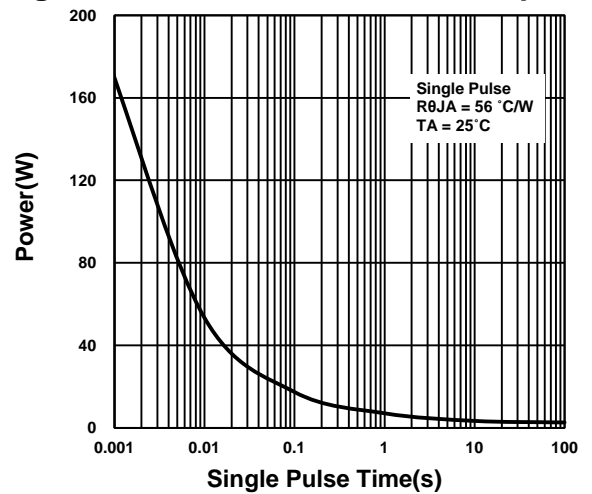
Source-Drain Diode Forward Voltage



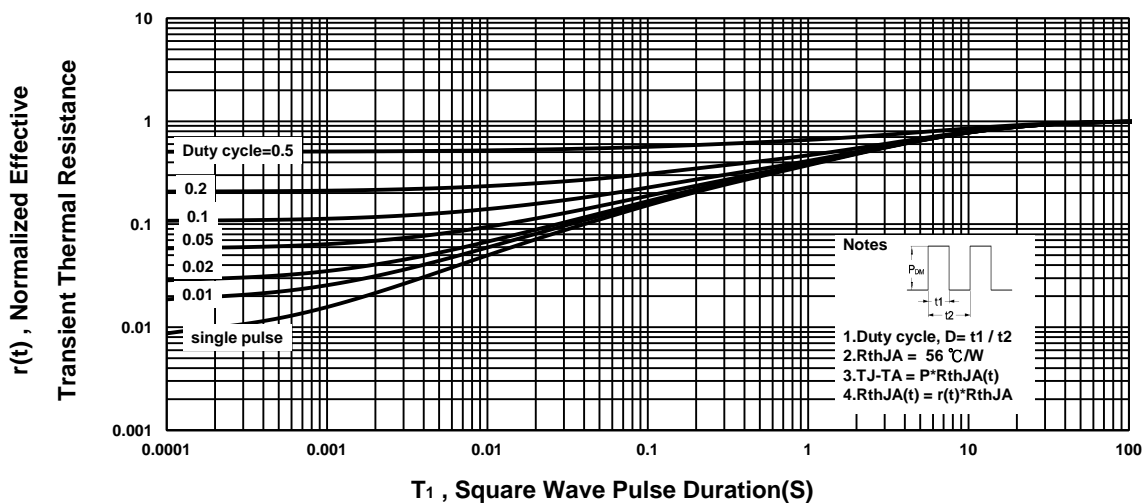
Safe Operating Area



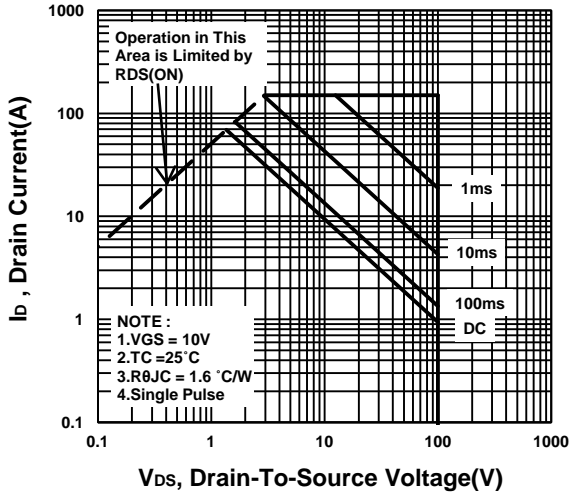
Single Pulse Maximum Power Dissipation



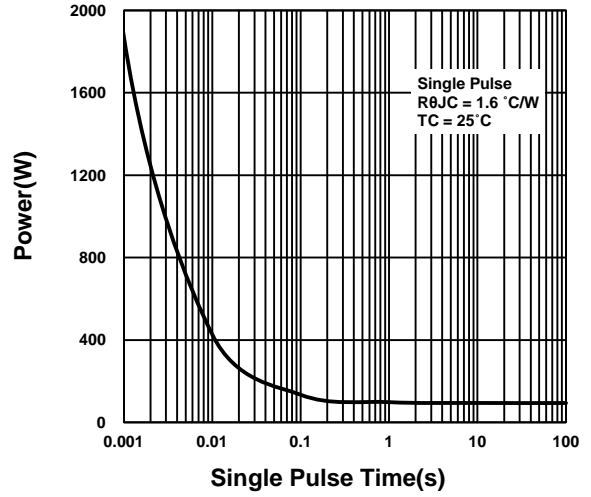
Transient Thermal Response Curve



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

